	1						
	Туре	L #	Hits	Search Text	DBs	Time Stamp	Comment s
8	BRS	L8	1753704	inductor or semiconductor or IC or (integrated adj circuit)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/08/2 9 15:07	
9	BRS	L9	26331	8 and passive and active	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/08/2 9 15:12	
10	BRS	L11	1262	9 and ((crib\$4 or cut\$6 or dic\$6) with substrate)	USPA T; US-P GPUB; JPO; DERW ENT; IBM_ TDB	2003/08/2 9 15:10	
12	BRS	L13	235	9 and (((crib\$4 or cut\$6 or dic\$6 or remove) with substrate) same (pad or bondpad))	USPA T; US-P GPUB; JPO; DERW ENT; IBM_ TDB	2003/08/2 9 15:11	

,5								
	Туре	L	#	Hits	S arch T xt	DBs	Time Stamp	Comment s
1	BRS	L1		23425	inductor and (semiconductor or IC or (integrated adj circuit))	USPA T; US-P GPUB; PPO; JPO; DERW ENT; IBM_ TDB	2003/08/2 9 14:34	
3	BRS	L3		3070	1 and (glass or glass-panel)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/08/2 9 14:34	
5	BRS	L 5		1639	3 and (crib\$4 or cut\$6 or dic\$6)	USPA T; US-P GPUB; FPO; JPO; DERW ENT; IBM_ TDB	2003/08/2 9 14:36	
6	BRS	L6		470	5 and passive and active	USPA T; US-P GPUB; ; EPO; JPO; DERW ENT; IBM_ TDB	2003/08/2 9 14:36	

	Туре	L #	Hits	Search Text	DBs	Time Stamp	Comment s
7	BRS	L7	262	6 and (pad or bondpad)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/08/2 9 14:36	

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	Туре	L #	Hits	S arch T xt	DBs	Time Stamp	Comment s
5	BRS	L5	483	planar adj induct\$4	USPA T; US-P GPUB; JPO; DERW ENT; IBM_ TDB	2003/08/2 9 11:44	
6	BRS	L6	118	5 and (scrib\$4 or cut\$6)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/08/2 9 11:44	
7	BRS	L7	27	6 and (pad or bondpad)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/08/2 9 11:45	